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# LE2416RDXA

## 16 kb I<sup>2</sup>C CMOS Serial EEPROM



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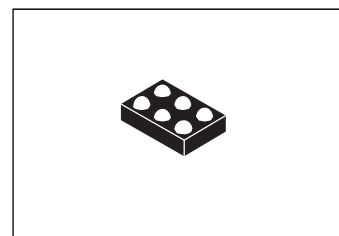
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### Overview

The LE2416RDXA is two-wire serial interface EEPROM (Electrically Erasable and Programmable ROM). This device realizes high speed and a high level reliability by high performance CMOS EEPROM technology. This device is compatible with I<sup>2</sup>C memory protocol, therefore it is best suited for application that requires re-writable nonvolatile parameter memory.

### Function

- Capacity : 16k bits (2k × 8 bits)
- Single supply voltage : 1.7 V to 3.6 V
- Operating temperature : -40 °C to +85 °C
- Interface : Two wire serial interface (I<sup>2</sup>C Bus\*)
- Operating clock frequency : 400 kHz (Fast), 1000 kHz (Fast-Plus)
- Low Power consumption
  - : Standby : 2 μA (max.)
  - : Active (Read, 400 kHz) : 0.5 mA (max.)
  - : Active (Read, 1000 kHz) : 2.0 mA (max.)
- Automatic page write mode : 16 Bytes
- Read mode : Sequential Read and random read
- Erase/Write cycles : 10<sup>6</sup> cycles (Page Write)
- Data Retention : 20 years
- Pull-up resistance: 5 kΩ (typ.) on WP pin with a built-in pull-up resistor
- High reliability : Adopts proprietary symmetric memory array configuration (USP6947325)
  - Hardware write protect feature
  - Noise filters connected to SCL and SDA pins
  - Incorporates a feature to prohibit write operations under low voltage conditions.
- Package : LE2416RDXA WLP6(0.80×1.20) 0.33 mm height



WLCSP6, 0.80x1.20

### Specifications

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Supply voltage			-0.5 to +4.6	V
DC input voltage			-0.5 to V <sub>DD</sub> +0.5	V
Over-shoot voltage			-1.0 to V <sub>DD</sub> +1.0	V
Storage temperature	Tstg		-65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

\* This product is licensed from Silicon Storage Technology, Inc. (USA).

### ORDERING INFORMATION

See detailed ordering and shipping information on page 17 of this data sheet.

## Recommended Operating Conditions

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Operating supply voltage			1.7		3.6	V
Operating temperature			-40		+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC Electrical Characteristics

Parameter	Symbol	Conditions	Spec.			Unit
			min	typ	max	
Supply current at reading	$I_{CC1}$	$f = 400 \text{ kHz}, V_{DD} = V_{DD} \text{ Max}$			0.5	mA
		$f = 1000 \text{ kHz}, V_{DD} = V_{DD} \text{ Max}$			2.0	
Supply current at writing	$I_{CC2}$	$f = 1000 \text{ kHz} / 400 \text{ kHz},$ $t_{WC} = 5 \text{ ms}, V_{DD} = V_{DD} \text{ Max}$			3.0	mA
Standby current	$I_{SB}$	$WP = V_{DD2} = V_{DD}$ $V_{IN} = V_{DD} \text{ or } V_{SS}$			2	$\mu\text{A}$
Input leakage current	$I_{LI}$	$V_{IN} = V_{SS} \text{ to } V_{DD}, V_{DD} = V_{DD} \text{ Max}$	-2.0		+2.0	$\mu\text{A}$
Output leakage current	$I_{LO}$	$V_{IN} = V_{SS} \text{ to } V_{DD}, V_{DD} = V_{DD} \text{ Max}$	-2.0		+2.0	$\mu\text{A}$
Input Low voltage	$V_{IL}$				$V_{DD} \times 0.3$	V
Input High voltage	$V_{IH}$		$V_{DD} \times 0.7$			V
Output Low voltage	$V_{OL2}$	$I_{OL} = 1.0 \text{ mA}, V_{DD} = 1.7 \text{ V}$			0.2	V
		$I_{OL} = 1.2 \text{ mA}, V_{DD} = 2.0 \text{ V}$				
	$V_{OL1}$	$I_{OL} = 2.1 \text{ mA}, V_{DD} = 2.0 \text{ V}$			0.4	V
		$I_{OL} = 3.0 \text{ mA}, V_{DD} = 2.5 \text{ V}$				

## Capacitance at $T_a = 25^\circ\text{C}$ , $f = 1 \text{ MHz}$

Parameter	Symbol	Conditions	max	Unit
In/Output pin capacitance	$C_{I/O}$	$V_{I/O} = 0 \text{ V (SDA)}$	10	pF
Input pin capacitance	$C_I$	$V_{IN} = 0 \text{ V}$	10	pF

Note : These parameter values do not represent the results of measurements undertaken for all devices but rather values for some of the sampled devices.

## Pull-up resistance (WP) at $T_a = -40$ to $85^\circ\text{C}$

Parameter	Symbol	Conditions	min	typ	max	Unit
Pull up resistance	R	Resistance between WP to $V_{DD2}$	3500	5000	6500	$\Omega$

Note : These parameter values do not represent the results of measurements undertaken for all devices but rather values for some of the sampled devices.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

**Fast-Plus (1000 kHz)**

Parameter	Symbol	Spec.			Unit
		min	typ	max	
Slave mode SCL clock frequency	$f_{SCLS}$	0		1000	kHz
SCL clock low time	$t_{LOW}$	500			ns
SCL clock high time	$t_{HIGH}$	300			ns
SDA output delay time	$t_{AA}$	50		450	ns
SDA data output hold time	$t_{DH}$	50			ns
Start condition setup time	$t_{SU,STA}$	250			ns
Start condition hold time	$t_{HD,STA}$	250			ns
Data in setup time	$t_{SU,DAT}$	50			ns
Data in hold time	$t_{HD,DAT}$	0			ns
Stop condition setup time	$t_{SU,STO}$	250			ns
SCL SDA rise time	$t_R$			120	ns
SCL SDA fall time	$t_F$			120	ns
Bus release time	$t_{BUF}$	500			ns
Noise suppression time	$t_{SP}$			50	ns
Write time	$t_{WC}$			5	ms

**Fast (400 kHz)**

Parameter	Symbol	Spec.			Unit
		min	typ	max	
Slave mode SCL clock frequency	$f_{SCLS}$	0		400	kHz
SCL clock low time	$t_{LOW}$	1200			ns
SCL clock high time	$t_{HIGH}$	600			ns
SDA output delay time	$t_{AA}$	100		900	ns
SDA data output hold time	$t_{DH}$	100			ns
Start condition setup time	$t_{SU,STA}$	600			ns
Start condition hold time	$t_{HD,STA}$	600			ns
Data in setup time	$t_{SU,DAT}$	100			ns
Data in hold time	$t_{HD,DAT}$	0			ns
Stop condition setup time	$t_{SU,STO}$	600			ns
SCL SDA rise time	$t_R$			300	ns
SCL SDA fall time	$t_F$			300	ns
Bus release time	$t_{BUF}$	1200			ns
Noise suppression time	$t_{SP}$			50	ns
Write time	$t_{WC}$			5	ms

**Standard (100 kHz)**

Parameter	Symbol	Spec.			Unit
		min	typ	max	
Slave mode SCL clock frequency	$f_{SCLS}$	0		100	kHz
SCL clock low time	$t_{LOW}$	4700			ns
SCL clock high time	$t_{HIGH}$	4000			ns
SDA output delay time	$t_{AA}$	100		3500	ns
SDA data output hold time	$t_{DH}$	100			ns
Start condition setup time	$t_{SU,STA}$	4700			ns
Start condition hold time	$t_{HD,STA}$	4000			ns
Data in setup time	$t_{SU,DAT}$	250			ns
Data in hold time	$t_{HD,DAT}$	0			ns
Stop condition setup time	$t_{SU,STO}$	4000			ns
SCL SDA rise time	$t_R$			1000	ns
SCL SDA fall time	$t_F$			300	ns
Bus release time	$t_{BUF}$	4700			ns
Noise suppression time	$t_{SP}$			50	ns
Write time	$t_{WC}$			5	ms

**AC measurement condition**

Input pulse level	$0.2 \times V_{DD}$ to $0.8 \times V_{DD}$
Input pulse rise / fall time	20 ns
Output timing reference level	$0.5 \times V_{DD}$
Output load	100 pF

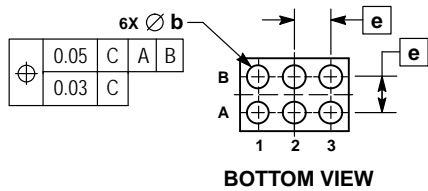
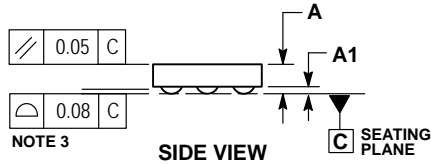
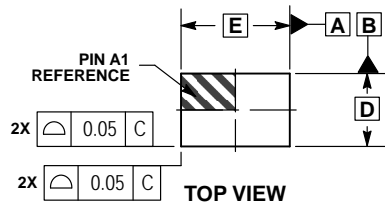
# Package Dimensions

unit : mm

## WLCSP6, 0.80x1.20

CASE 567HM

ISSUE O

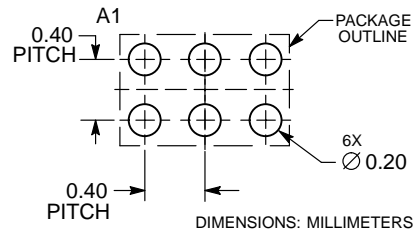


### NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

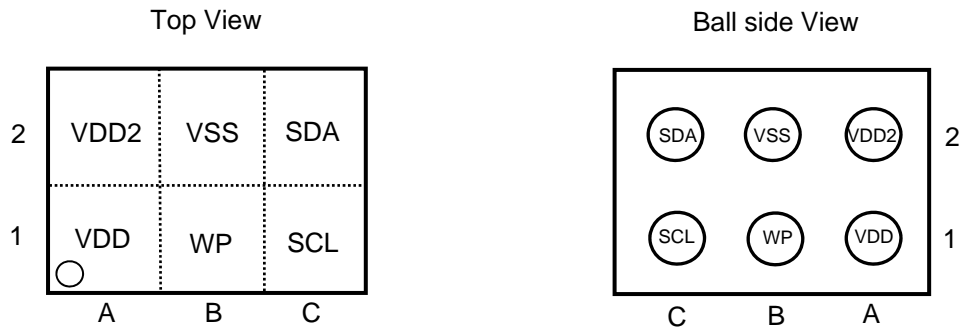
MILLIMETERS		
DIM	MIN	MAX
A	---	0.33
A1	0.03	0.13
b	0.15	0.25
D	0.80 BSC	
E	1.20 BSC	
e	0.40 BSC	

### RECOMMENDED SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

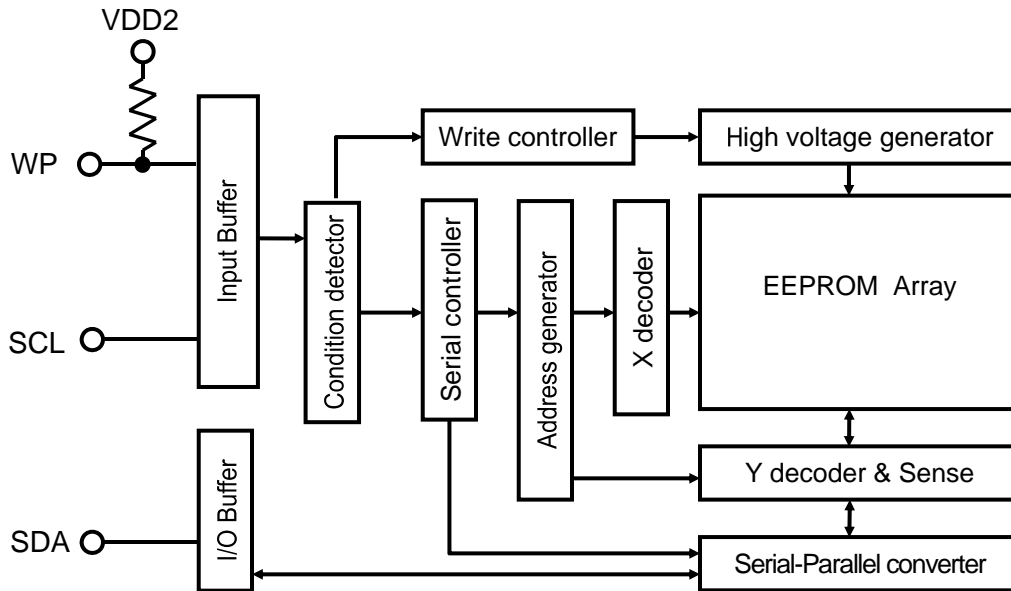
# Pin Assignment



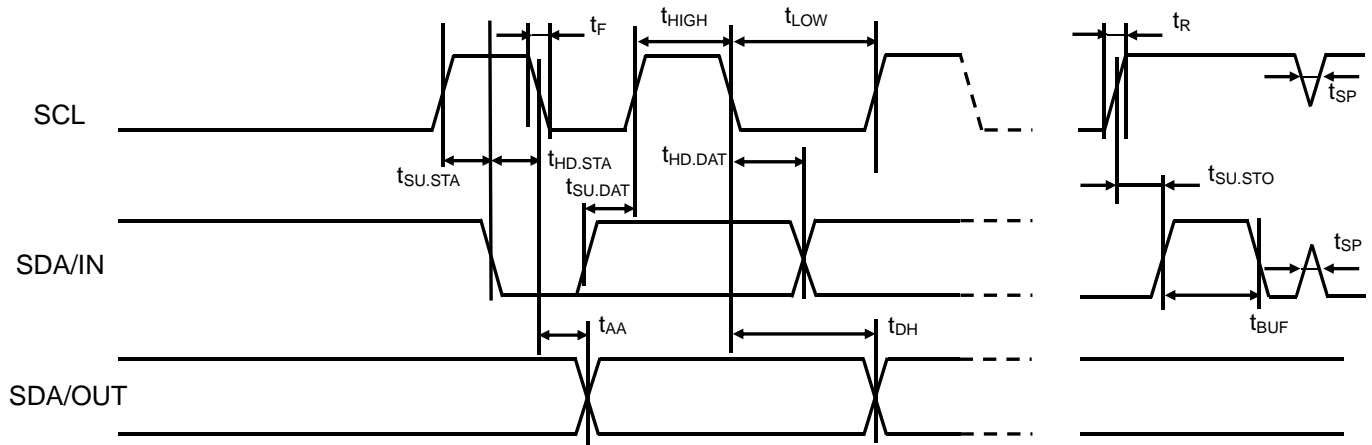
## Pin Descriptions

PIN.A1	VDD	Power supply
PIN.A2	VDD2	Power supply for WP pin Pull-up
PIN.B1	WP	Write protect
PIN.B2	VSS	Ground
PIN.C1	SCL	Serial clock input
PIN.C2	SDA	Serial data input/output

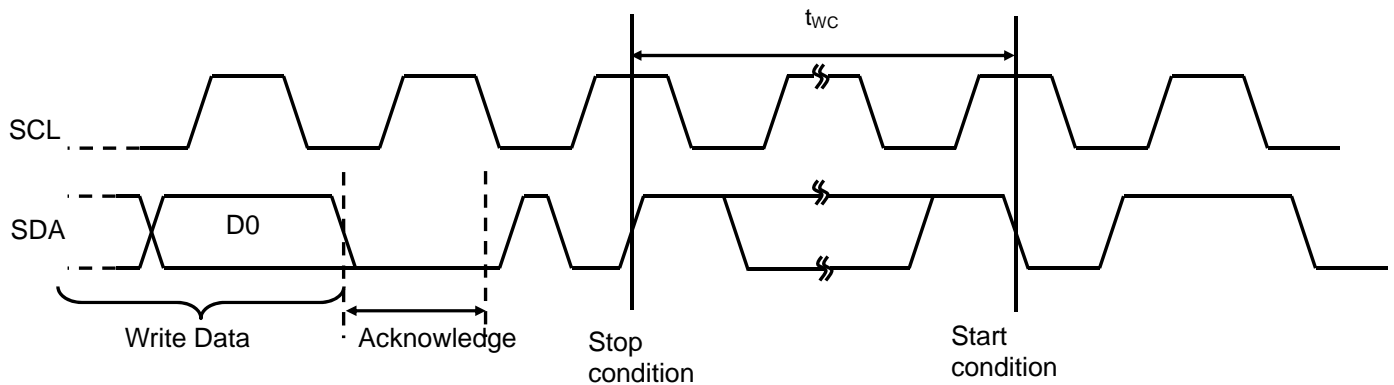
## Block Diagram



## Bus timing



## Write timing



## Pin Function

### SCL (Serial clock)

The SCL signal is used to control serial input data timing. The SCL is used to latch input data synchronously at the rising edge and read output data synchronously at the falling edge.

### SDA (Serial input / output data)

The SDA pin is bidirectional for serial data transfer. It is an open-drain structure that needs to be pulled up by resistor.

### WP (Write protect)

When the WP input is high, write protection is enabled. When WP input is either low or floating, write protection is disabled. The read operation is always activated irrespective of the WP pin status.

### V<sub>DD2</sub> (Power supply for WP pin pull-up)

V<sub>DD2</sub> pin is for the pull-up power supply to WP pin. Voltage impression of  $-0.5\text{ V}$  to  $V_{DD} + 0.5\text{ V}$  is permitted like other pins about the pin voltage.



## Functional Description

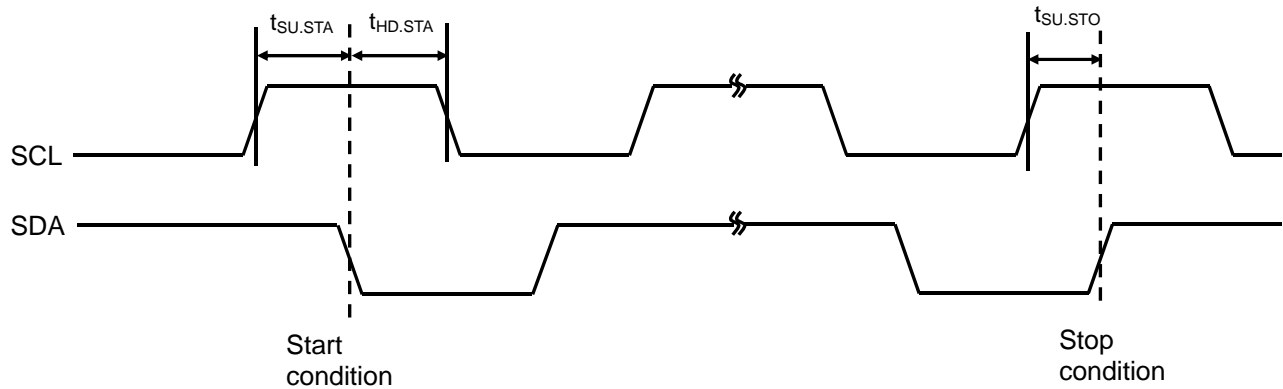
The device supports the I<sup>2</sup>C protocol. Any device that sends data on to the bus is defined to be a transmitter, and any device that reads the data to a receiver. The device that controls the data transfer is known as the bus master, and the other as the slave device.

### 1) Start Condition

A Start condition needs to start the EEPROM operation, it is to set falling edge of the SDA while the SCL is stable in the high status.

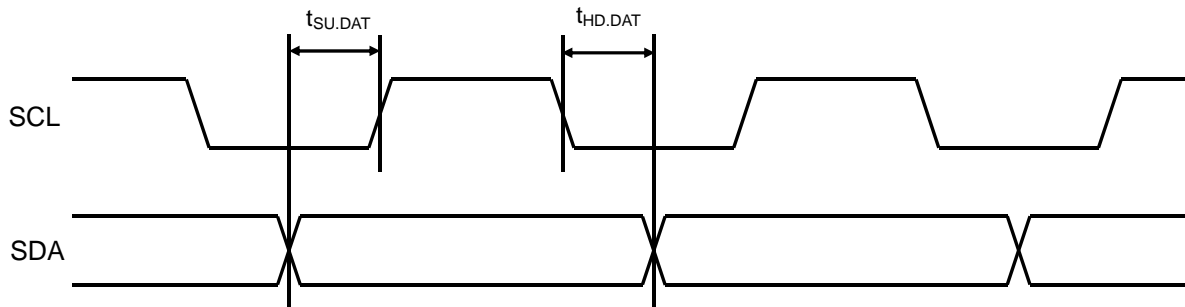
### 2) Stop Condition

A Stop condition is identified by rising edge of the SDA signal while the SCL is stable in the high status. The device becomes the standby mode from a Read operation by a Stop condition. In a write sequence, a stop condition is trigger to terminate the write data inputs and it is trigger to start the internal write cycle. After the internally write cycle time which is specified as  $t_{WC}$ , the device enters a standby mode.



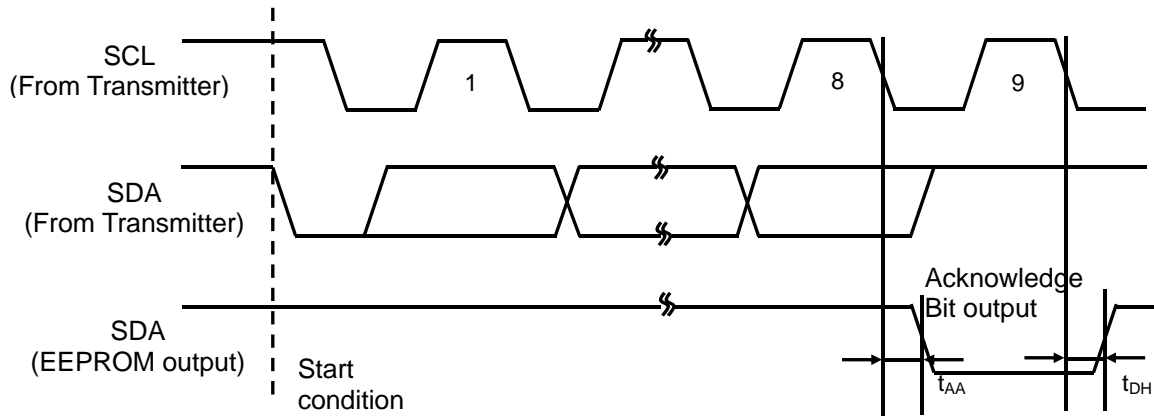
### 3) Data Input

During data input, the device latches the SDA on the rising edge of the SCL. For correct the operation, The SDA must be stable during the rising edge of the SCL.



#### 4) Acknowledge Bit (ACK)

The Acknowledge Bit is used to indicate a successful byte data transfer. The receiver sends a zero to acknowledge that it has received each word (Device Code, Slave Address etc) from the transmitter.

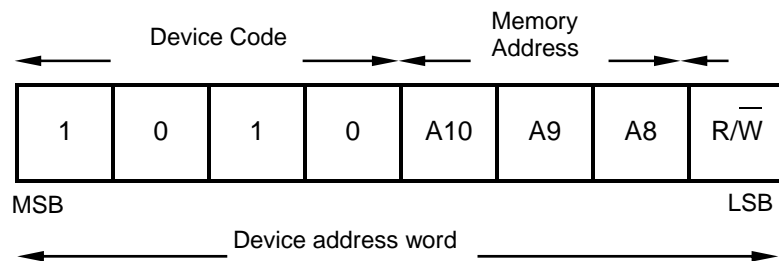


#### 5) Device addressing

To transmit between the bus master and slave device (EEPROM), the master must send a Start condition to the EEPROM. The device address word of the EEPROM consists of 4-bit Device Code, 3-bit Memory address and 1-bit read/write code. By sending these, it becomes possible to communicate between the bus master and the EEPROM.

The upper 4-bit of the device address word are called the Device Code, the Device Code of the EEPROM uses 1010b fixed code. This device does not have the Slave address.

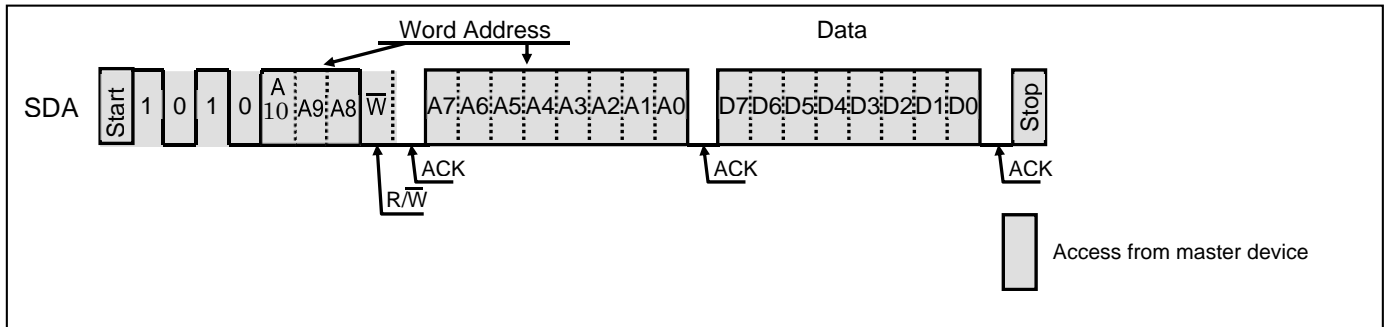
When the Device Code and Memory address (A10, A9, A8) are received on the SDA, the device only responds. The 8<sup>th</sup> bit is the read/write bit. The bit is set to 1 for Read operation and 0 for Write operation. If a match occurs on the Device Code, the corresponding device gives an acknowledgement on SDA during the 9<sup>th</sup> bit time. If device does not match the Device Code, it deselects itself from the bus, and goes into the Standby mode.



## 6) EEPROM Write Operation

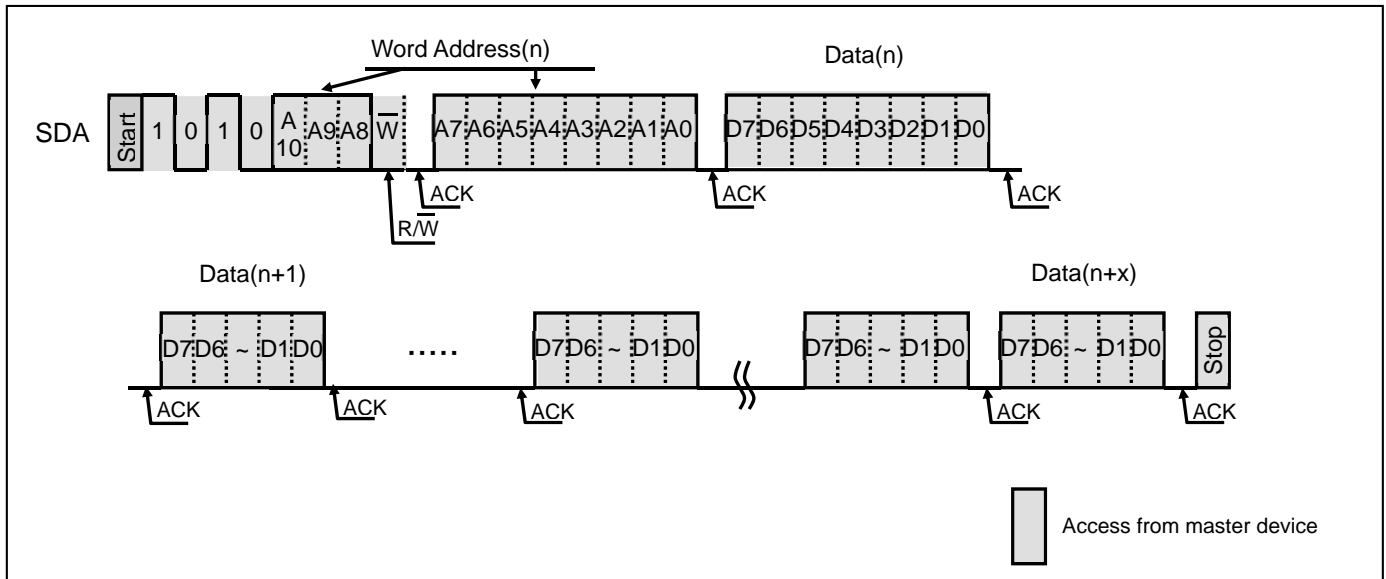
### 6)-1. Byte Write

The write operation requires a 7-bit device address (Device code + A10 + A9 + A8) with the 8<sup>th</sup> bit = 0 (write). Then the EEPROM sends acknowledgement 0 at the 9<sup>th</sup> clock cycle. After these, the EEPROM receives word address (A7 to A0), and the EEPROM outputs acknowledgement 0. Then the EEPROM receives 8-bit write data, the EEPROM outputs acknowledgement 0 after receipt of write data. If the EEPROM receives a stop condition, the EEPROM enters an internally timed (tWC) write cycle and terminates receipt of inputs until completion of the write cycle.



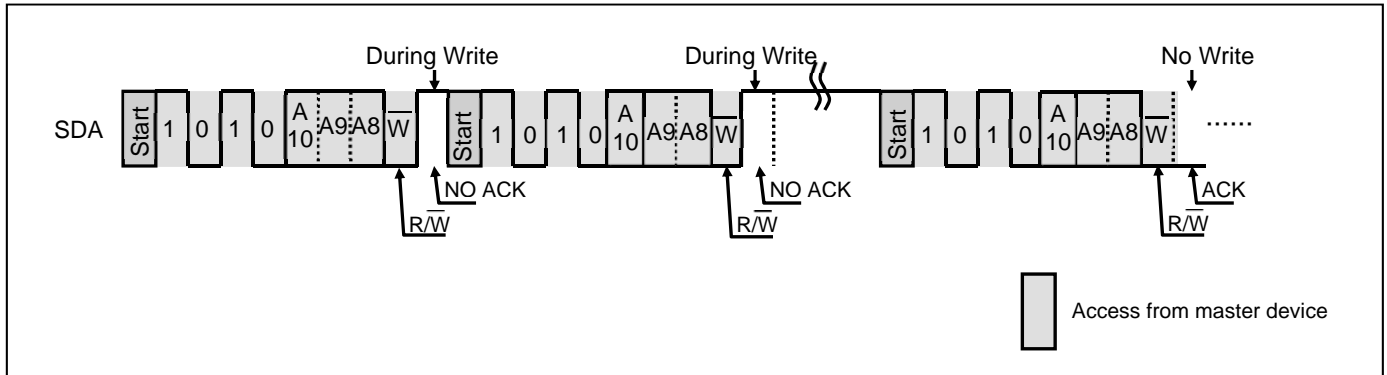
### 6)-2. Page Write

The Page write allows up to 16 bytes to be written in a single write cycle. The page write is the same sequence as the byte write except for inputting the more write data. The page write is initiated by a start condition, device code, memory address and write data(n) with every 9<sup>th</sup> bit acknowledgement. The device enters the page write operation if this device receives more write data(n+1) instead of receiving a stop condition. The page address (A0 to A3) bits are automatically incremented on receiving write data(n+1). The device can continue to receive write data up to 16 bytes. If the page address bits reaches the last address of the page, the page address bits will roll over to the first address of the same page and previous write data will be overwritten. After these, if the device receives a stop condition, the device enters an internally timed (tWCx(n+x)) write cycle and terminates receipt of inputs until completion of the write cycle.



### 6)-3. Acknowledge Polling

The Acknowledge Polling operation is used to show if the EEPROM is in an internally timed write cycle or not. This operation is initiated by the stop condition after inputting write data. This requires the 8-bit device address word with the 8<sup>th</sup> bit = 0 (write) following the start condition during an internally timed write cycle. If the EEPROM is busy with the internal write cycle, no acknowledge will be returned. If the EEPROM has terminated the internal write cycle, it responds with an acknowledge. The terminated write cycle of the EEPROM can be known by this operation.



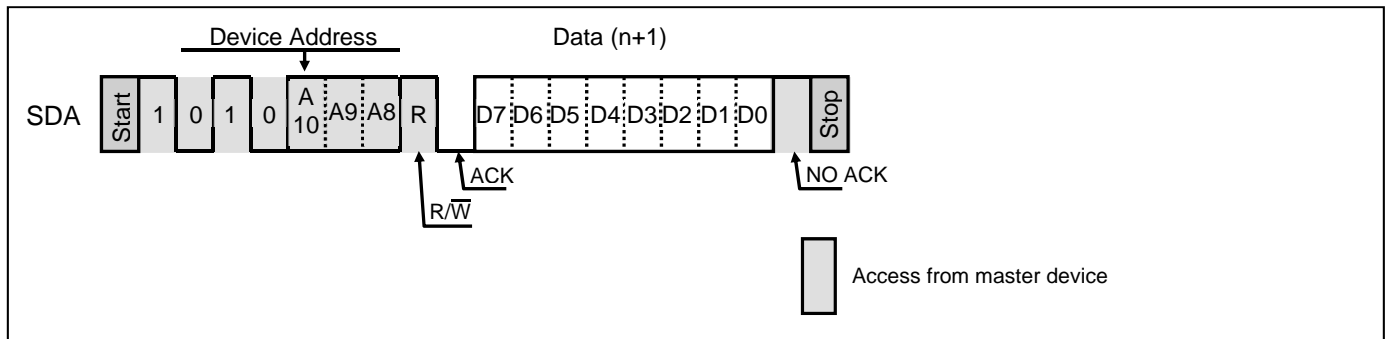
## 7) EEPROM Read Operation

### 7)-1. Current Address Read

The device has an internal address counter. It maintains that last address during the last read or write operation, with incremented by one. The current address read accesses the address kept by the internal address counter. After receiving a start condition and the device address word with the 8<sup>th</sup> bit = 1 (Read), the EEPROM outputs the 8-bit current address data from following acknowledgement 0. If the EEPROM receives acknowledgement 1 and a following stop condition, the EEPROM stops the read operation and is returned to a standby mode. In case the EEPROM has accessed the last address of the last page at previous read operation, the current address will roll over and returns to zero address. In case EEPROM has accessed the last address of the last page at previous write operation, the current address roll over within page addressing and returns to the first address in the same page.

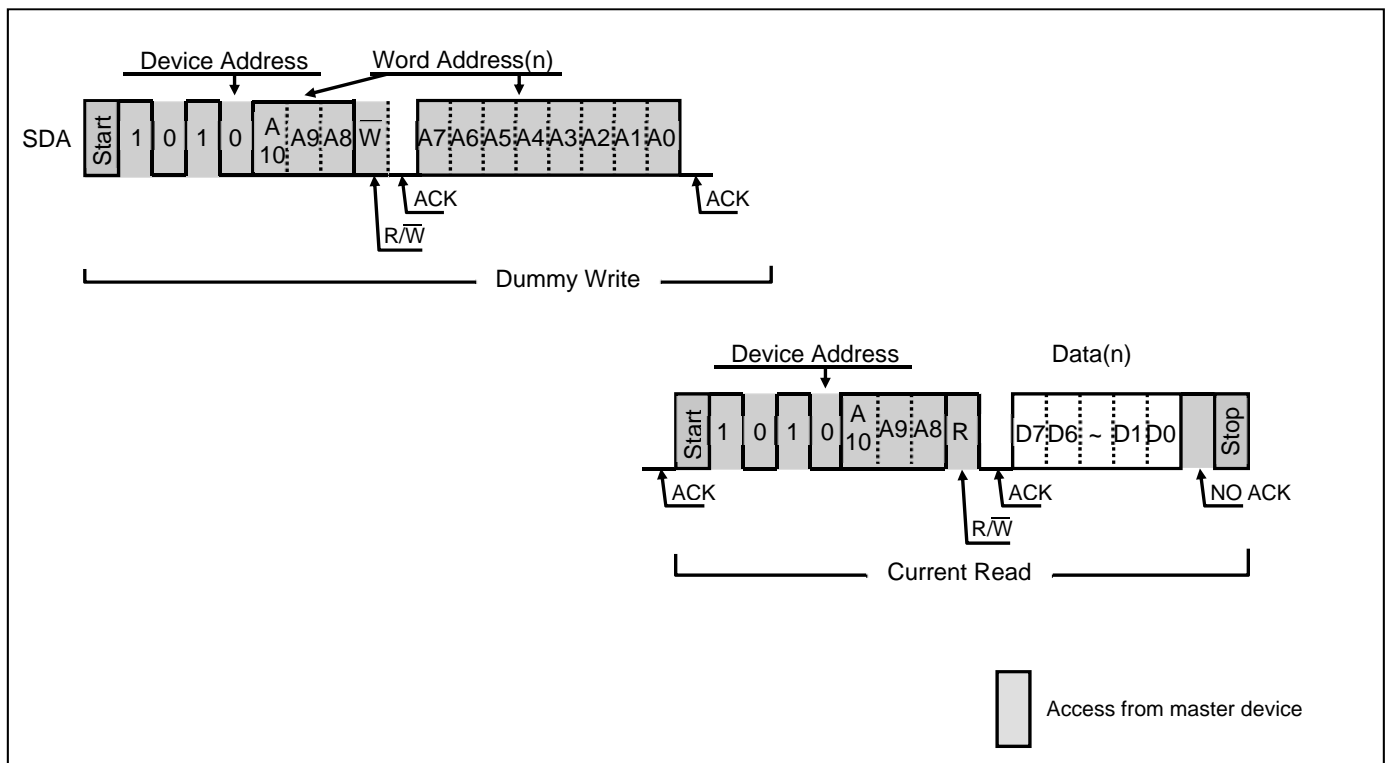
The current address is valid while power is on. After power on, the current address will be reset (all 0).

Note: After the page write operation, the current address is the specified memory address in the last page write, if the write data is more than 16-bytes.



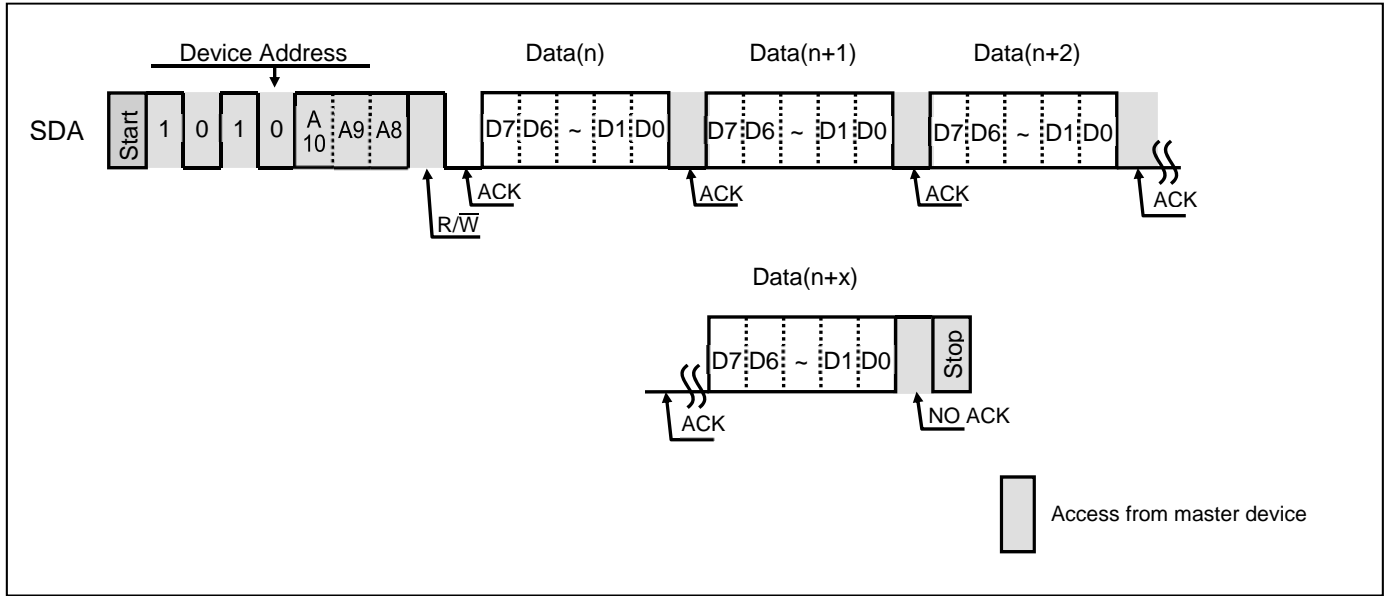
### 7)-2. Random Read

The random read requires a dummy write to set read address. The EEPROM receives a start condition and the device address (Device code + A10 + A9 + A8) with the 8<sup>th</sup> bit = 0 (write), the memory address. The EEPROM outputs acknowledgement 0 after receiving memory address then enters a current address read with receiving a start condition. The EEPROM outputs the read data of the address which was defined in the dummy write operation. After receiving no acknowledgement and a following stop condition, the EEPROM stops the random read operation and returns to a standby mode.



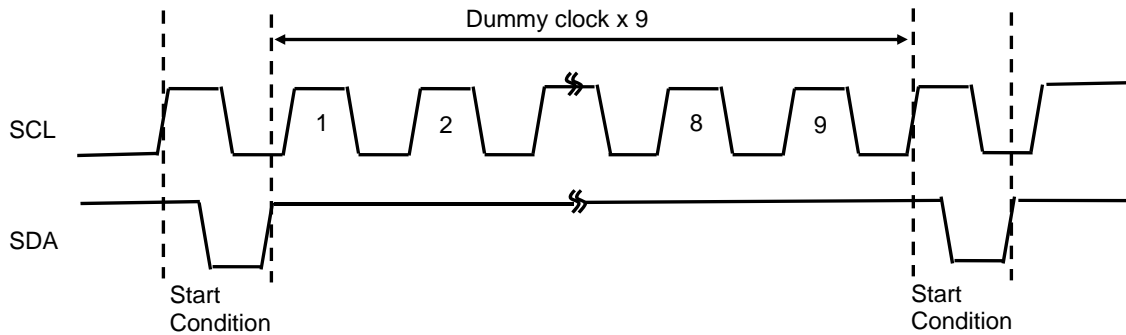
### 7)-3. Sequential Read

The sequential read operation is initiated by either a current address read or random read. If the EEPROM receives acknowledgement 0 after 8-bit read data, the read address is incremented and the next 8-bit read data outputs. The current address will roll over and returns address zero if it reaches the last address of the last page. The sequential read can be continued after roll over. The sequential read is terminated if the EEPROM receives no acknowledgement and a following stop condition.



### 1) Software reset function

Software reset (start condition + 9 dummy clock cycles + start condition), shown in the figure below, is executed in order to avoid erroneous operation after power-on and to reset while the command input sequence. During the dummy clock input period, the SDA bus must be opened (set to high by a pull-up resistor). Since it is possible for the ACK output and read data to be output from the EEPROM during the dummy clock period, forcibly entering H will result in an overcurrent flow. Note that this software reset function does not work during the internal write cycle.



### 2) Pull-up resistor of SDA pin

Due to the demands of the I<sup>2</sup>C bus protocol function, the SDA pin must be connected to a pull-up resistor (with a resistance from several kΩ to several tens of kΩ) without fail. The appropriate value must be selected for this resistance ( $R_{PU}$ ) on the basis of the  $V_{IL}$  and  $I_{IL}$  of the microcontroller and other devices controlling this product as well as the  $V_{OL} - I_{OL}$  characteristics of the product. Generally, when the resistance is too high, the operating frequency will be restricted; conversely, when it is too low, the operating current consumption will increase.

#### $R_{PU}$ maximum value

The maximum resistance must be set in such a way that the bus potential, which is determined by the sum total ( $I_L$ ) of the input leaks of the devices connected to the SDA bus and by  $R_{PU}$ , can completely satisfy the input high level ( $V_{IH}$  min) of the microcontroller and EEPROM. However, a resistance value that satisfies SDA rise time  $t_R$  and fall time  $t_F$  must be set.

$$R_{PU} \text{ maximum value} = (V_{DD} - V_{IH}) / I_L$$

Example: When  $V_{DD} = 3.0 \text{ V}$  and  $I_L = 2 \mu\text{A}$

$$R_{PU} \text{ maximum value} = (3.0 \text{ V} - 3.0 \text{ V} \times 0.8) / 2 \mu\text{A} = 300 \text{ k}\Omega$$

#### $R_{PU}$ minimum value

A resistance corresponding to the low-level output voltage ( $V_{OL}$  max) of EEPROM must be set.

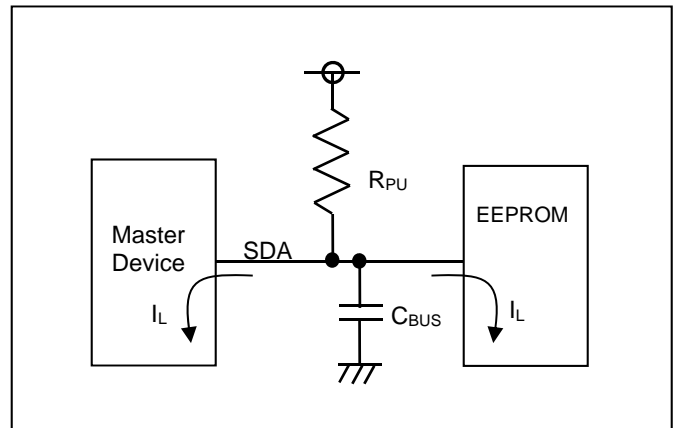
$$R_{PU} \text{ minimum value} = (V_{DD} - V_{OL}) / I_{OL}$$

Example: When  $V_{DD} = 3.0 \text{ V}$ ,  $V_{OL} = 0.4 \text{ V}$  and  $I_{OL} = 1 \text{ mA}$

$$R_{PU} \text{ minimum value} = (3.0 \text{ V} - 0.4) / 1 \text{ mA} = 2.6 \text{ k}\Omega$$

#### Recommended $R_{PU}$ setting

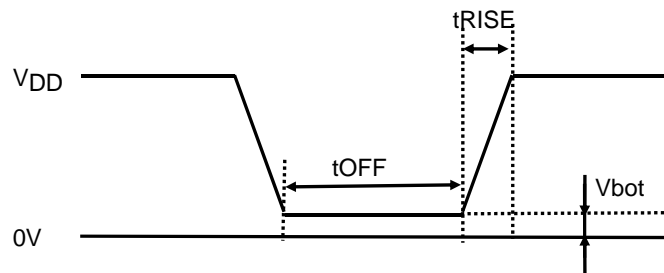
$R_{PU}$  is set to strike a good balance between the operating frequency requirements and power consumption. If it is assumed that the SDA load capacitance is 50 pF and the SDA output data strobe time is 500 ns,  $R_{PU}$  will be about  $R_{PU} = 500 \text{ ns} / 50 \text{ pF} = 10 \text{ k}\Omega$ .



### 3) Precautions when turning on the power

This product contains a power-on reset circuit for preventing the inadvertent writing of data when the power is turned on. The following conditions must be met in order to ensure stable operation of this circuit. No data guarantees are given in the event of an instantaneous power failure during the internal write operation.

symbol	Parameter	Spec.			Unit
		Min.	Typ.	Max.	
$t_{RISE}$	Power rise time	–	–	100	ms
$t_{OFF}$	Power off time	10	–	–	ms
$V_{bot}$	Power bottom voltage	–	–	0.2	V

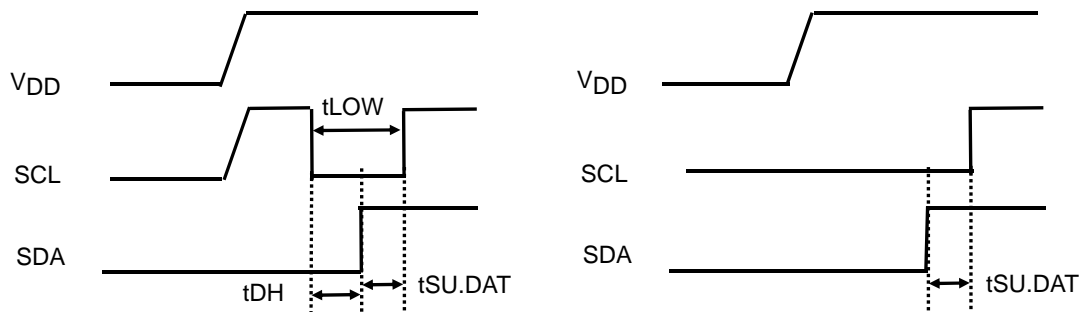


Notes:

- 1) The SDA pin must be set to high and the SCL pin to low or high.
- 2) Steps must be taken to ensure that the SDA and SCL pins are not placed in a high-impedance state.

#### A. If it is not possible to satisfy the instruction 1 in Note above, and SDA is set to low during power rise

After the power has stabilized, the SCL and SDA pins must be controlled as shown below, with both pins set to high.



#### B. If it is not possible to satisfy the instruction 2 in Note above

After the power has stabilized, software reset must be executed.

#### C. If it is not possible to satisfy the instructions both 1 and 2 in Note above

After the power has stabilized, the steps in A must be executed, then software reset must be executed.

### 4) Noise filter for the SCL and SDA pins

This product contains a filter circuit for eliminating noise at the SCL and SDA pins. Pulses of 100 ns or less are not recognized because of this function.

### 5) Function to inhibit writing when supply voltage is low

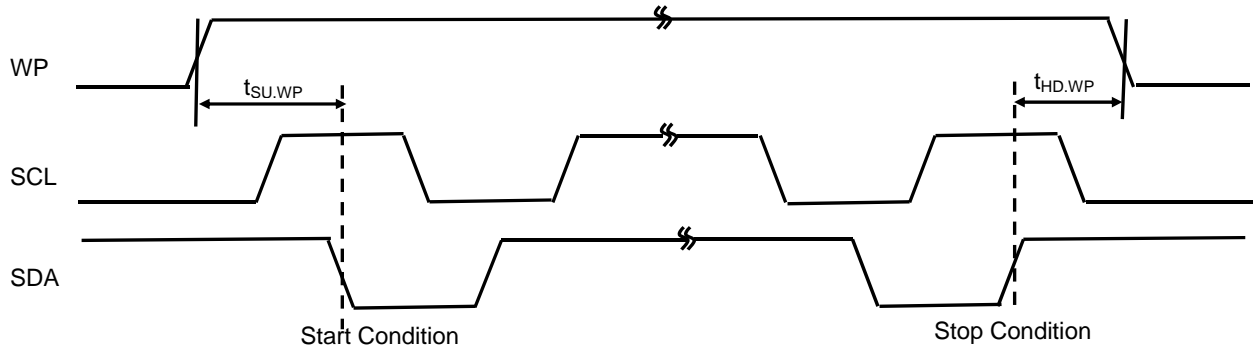
This product contains a supply voltage monitoring circuit that inhibits inadvertent writing below the guaranteed operating supply voltage range. The data is protected by ensuring that write operations are not started at voltages (typ.) of 1.3 V and below.



### 6) Notes on write protect operation

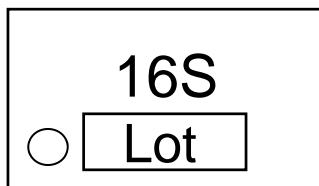
This product prohibits all memory array writing when the WP pin is high. To ensure full write protection, the WP is set high for all periods from the start condition to the stop condition, and the conditions below must be satisfied.

symbol	Parameter	Spec.			Unit
		Min.	Typ.	Max.	
$t_{SU.WP}$	WP Setup time	600	–	–	ns
$t_{HD.WP}$	WP Hold time	600	–	–	ns



## MARKING INFORMATION

LE2416RDXA WLP6(0.80x1.20)



Part ID : 16S  
Lot Number : 3digits

## ORDERING INFORMATION

Device	Package	Shipping (Qty / Packing)
LE2416RDXATDG	WLCSP6, 0.80x1.20 (Pb-Free / Halogen Free)	5000 / Tape & Reel

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. [http://www.onsemi.com/pub\\_link/Collateral/BRD8011-D.PDF](http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF)

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